

TOSHIBA Multi-Chip Device  
Silicon P-Channel MOS Type + N-Channel MOS Type

# SSM6E02TU

## ○Power Management Switch Applications

- 1.5 V drive
- P-channel MOSFET and N-channel MOSFET incorporated into one package.
- Low power dissipation due to P-channel MOSFET that features low R<sub>DS (ON)</sub> and low-voltage operation

## Q1 Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-Source voltage	V <sub>DS</sub>	-20	V
Gate-Source voltage	V <sub>GSS</sub>	± 8	V
Drain current	DC	I <sub>D</sub>	-1.8
	Pulse	I <sub>DP</sub> (Note 1)	-3.6

## Q2 Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-Source voltage	V <sub>DS</sub>	20	V
Gate-Source voltage	V <sub>GSS</sub>	± 10	V
Drain current	DC	I <sub>D</sub>	0.1
	Pulse	I <sub>DP</sub> (Note 1)	0.2

## Absolute Maximum Ratings (Q1, Q2 common) (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain power dissipation	P <sub>D</sub> (Note 2)	0.5	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature range	T <sub>stg</sub>	-55 to 150	°C

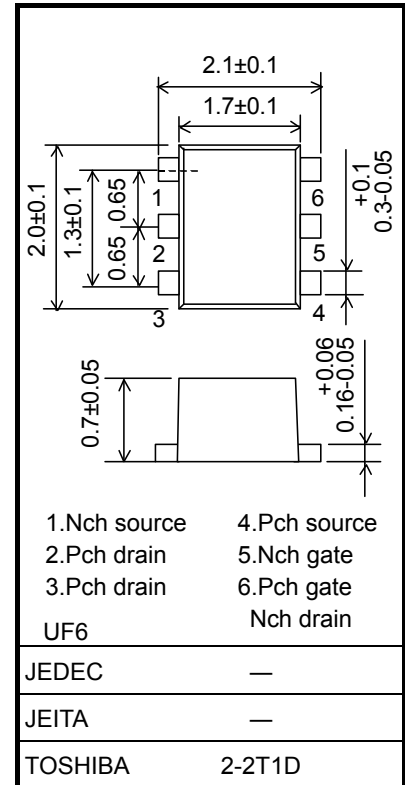
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width limited by maximum channel temperature.

Note 2: Mounted on an FR4 board (25.4 mm × 25.4 mm × 1.6 t, Cu pad: 645 mm<sup>2</sup>)

Unit: mm



Weight: 7.0 mg (typ.)

## Q1 Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit	
Drain-Source breakdown voltage	$V_{(BR)DSS}$	$I_D = -1 \text{ mA}, V_{GS} = 0$	-20	—	—	V	
	$V_{(BR)DSX}$	$I_D = -1 \text{ mA}, V_{GS} = +8 \text{ V}$	-12	—	—		
Drain cut-off current	$I_{DSS}$	$V_{DS} = -20 \text{ V}, V_{GS} = 0$	—	—	-10	$\mu\text{A}$	
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0$	—	—	$\pm 1$	$\mu\text{A}$	
Gate threshold voltage	$V_{th}$	$V_{DS} = -3 \text{ V}, I_D = -1 \text{ mA}$	-0.3	—	-1.0	V	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = -3 \text{ V}, I_D = -0.9 \text{ A}$ (Note 3)	2.7	5.4	—	S	
Drain-Source on-resistance	$R_{DS(ON)}$	$I_D = -1.0 \text{ A}, V_{GS} = -2.5 \text{ V}$ (Note 3)	—	95	136	m $\Omega$	
		$I_D = -1.0 \text{ A}, V_{GS} = -1.8 \text{ V}$ (Note 3)	—	122	204		
		$I_D = -0.1 \text{ A}, V_{GS} = -1.5 \text{ V}$ (Note 3)	—	137	364		
Input capacitance	$C_{iss}$	$V_{DS} = -10 \text{ V}, V_{GS} = 0$ $f = 1 \text{ MHz}$	—	568	—	pF	
Output capacitance	$C_{oss}$		—	75	—		
Reverse transfer capacitance	$C_{rss}$		—	67	—		
Switching time	Turn-on time	$t_{on}$	$V_{DD} = -10 \text{ V}, I_D = -0.9 \text{ A}$ $V_{GS} = 0 \text{ to } -2.5 \text{ V}, R_G = 4.7 \Omega$	—	29	—	ns
	Turn-off time	$t_{off}$		—	39	—	
Total gate charge	$Q_g$	$V_{DS} = -16 \text{ V}, I_{DS} = -1.8 \text{ A},$ $V_{GS} = -4 \text{ V}$	—	10.6	—	nC	
Gate-Source charge	$Q_{gs}$		—	7.4	—		
Gate-Drain charge	$Q_{gd}$		—	3.3	—		
Drain-Source forward voltage	$V_{DSF}$	$I_D = 1.8 \text{ A}, V_{GS} = 0$ (Note 3)	—	0.8	1.2	V	

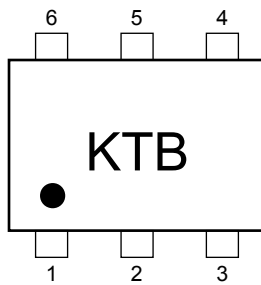
Note 3: Pulse test

## Q2 Electrical Characteristics (Ta = 25°C)

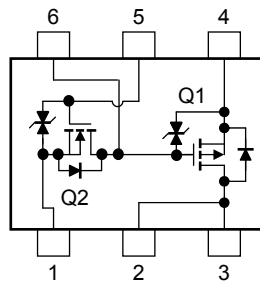
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit	
Drain-Source breakdown voltage	$V_{(BR)DSS}$	$I_D = 0.1 \text{ mA}, V_{GS} = 0$	20	—	—	V	
Drain cut-off current	$I_{DSS}$	$V_{DS} = 20 \text{ V}, V_{GS} = 0$	—	—	1	$\mu\text{A}$	
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$	—	—	$\pm 1$	$\mu\text{A}$	
Gate threshold voltage	$V_{th}$	$V_{DS} = 3 \text{ V}, I_D = 0.1 \text{ mA}$	0.6	—	1.1	V	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 3 \text{ V}, I_D = 10 \text{ mA}$ (Note 3)	40	—	—	mS	
Drain-Source on-resistance	$R_{DS(ON)}$	$I_D = 10 \text{ mA}, V_{GS} = 4 \text{ V}$ (Note 3)	—	1.5	3.0	$\Omega$	
		$I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$ (Note 3)	—	2.2	4.0		
		$I_D = 1 \text{ mA}, V_{GS} = 1.5 \text{ V}$ (Note 3)	—	5.2	15		
Input capacitance	$C_{iss}$	$V_{DS} = 3 \text{ V}, V_{GS} = 0$ $f = 1 \text{ MHz}$	—	9.3	—	pF	
Output capacitance	$C_{oss}$		—	9.8	—		
Reverse transfer capacitance	$C_{rss}$		—	4.5	—		
Switching time	Turn-on time	$t_{on}$	$V_{DD} = 3 \text{ V}, I_D = 10 \text{ mA}$ $V_{GS} = 0 \text{ to } 2.5 \text{ V}, R_G = 50 \Omega$	—	70	—	ns
	Turn-off time	$t_{off}$		—	125	—	

Note 3: Pulse test

**Marking**



**Equivalent Circuit (top view)**



**Precaution**

$V_{th}$  can be expressed as the voltage between the gate and source when the low operating current value is  $I_D = -1mA$  for this product. For normal switching operation,  $V_{GS (on)}$  requires a higher voltage than  $V_{th}$  and  $V_{GS (off)}$  requires a lower voltage than  $V_{th}$ . (The relationship can be established as follows:  $V_{GS (off)} < V_{th} < V_{GS (on)}$ .)

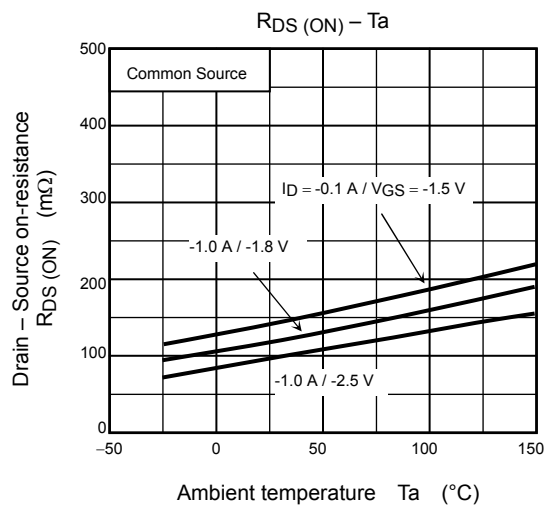
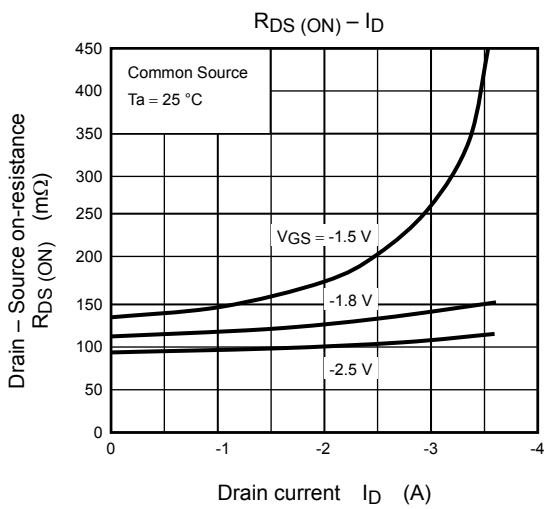
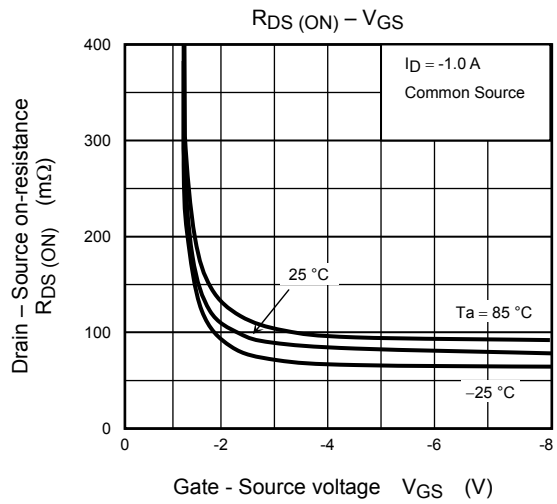
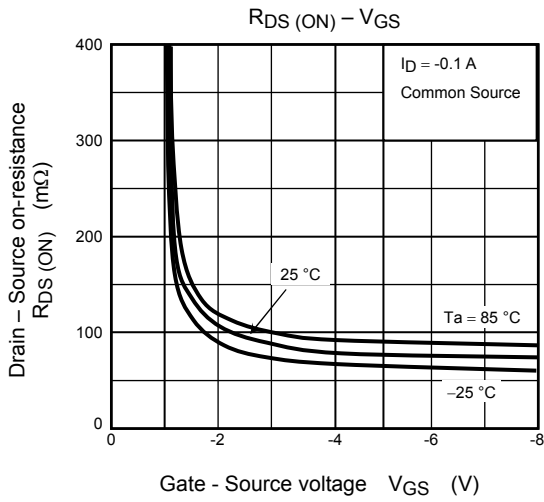
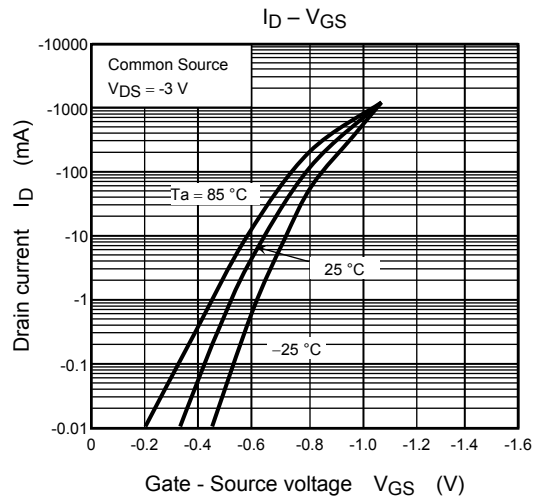
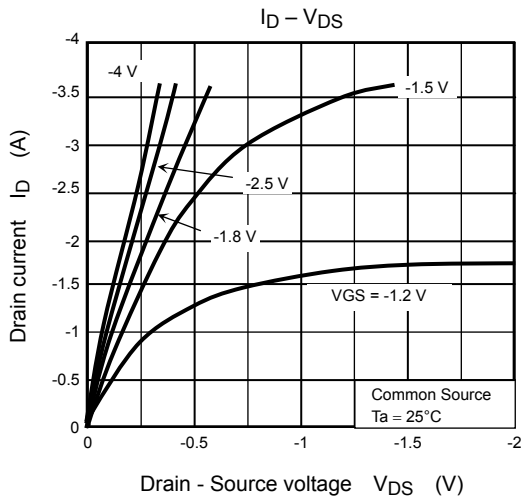
Be sure to take this into consideration when using the device.

**Handling Precaution**

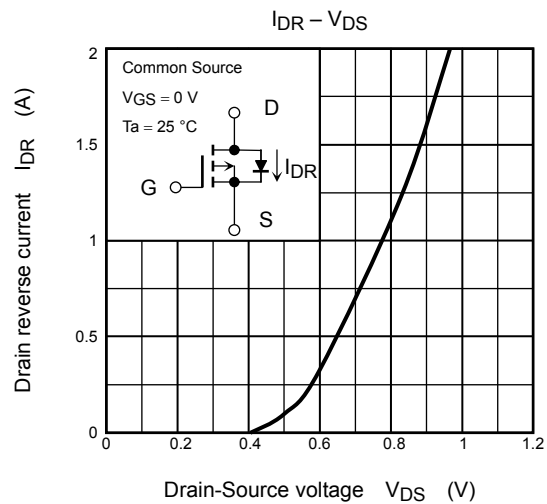
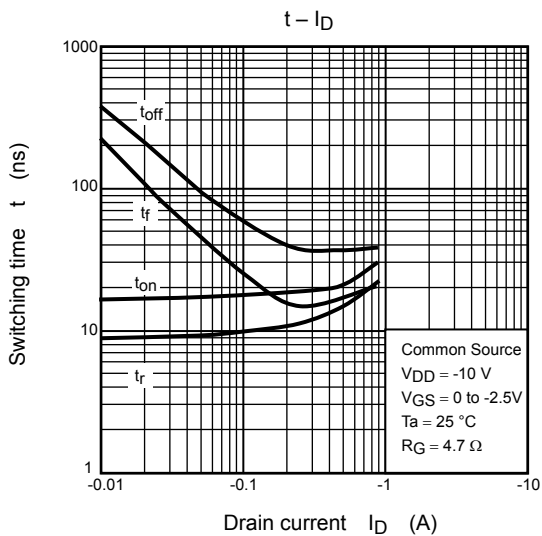
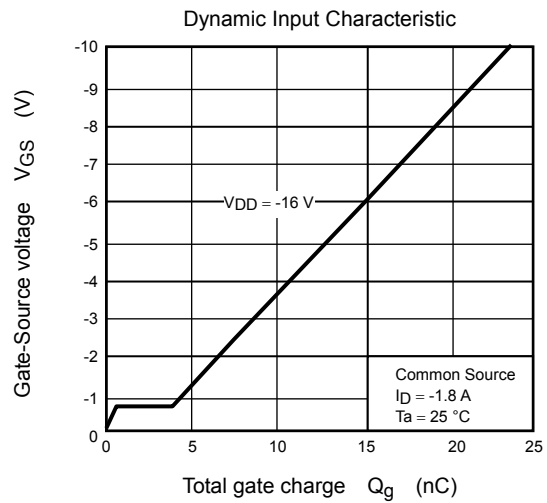
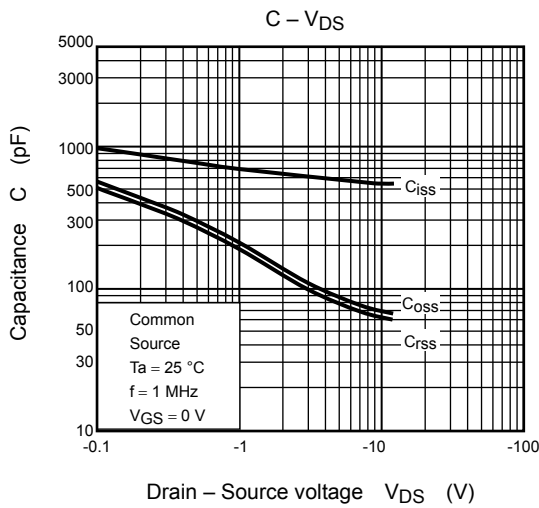
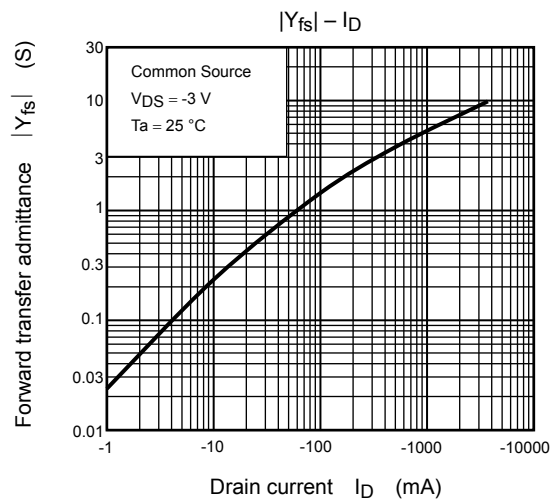
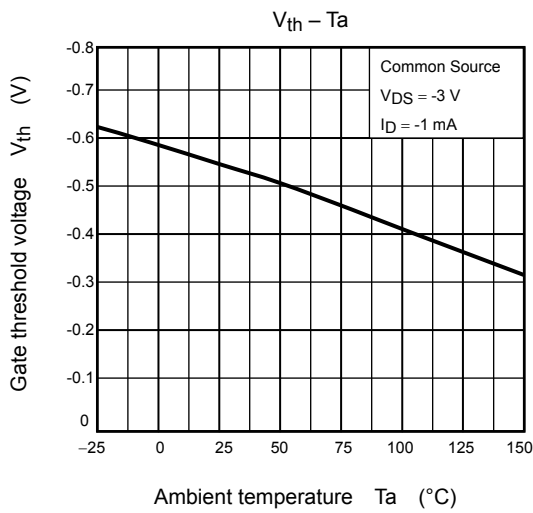
When handling individual devices (which are not yet mounted on a circuit board), ensure that the environment is protected against static electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

Thermal resistance  $R_{th (j-a)}$  and drain power dissipation  $P_D$  vary depending on board material, board area, board thickness and pad area. When using this device, please take heat dissipation into consideration.

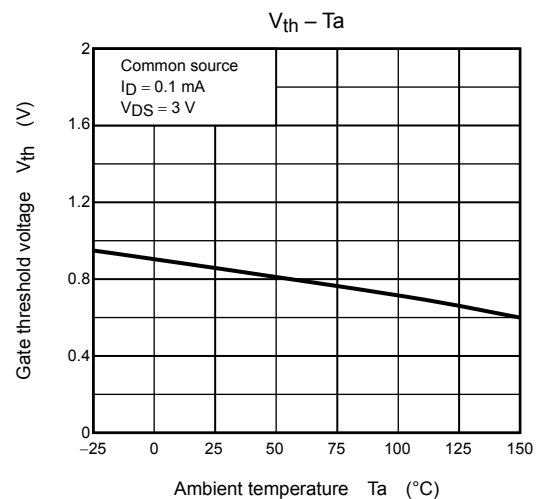
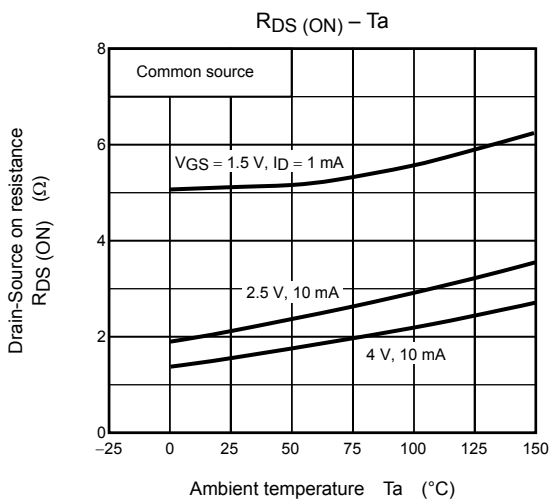
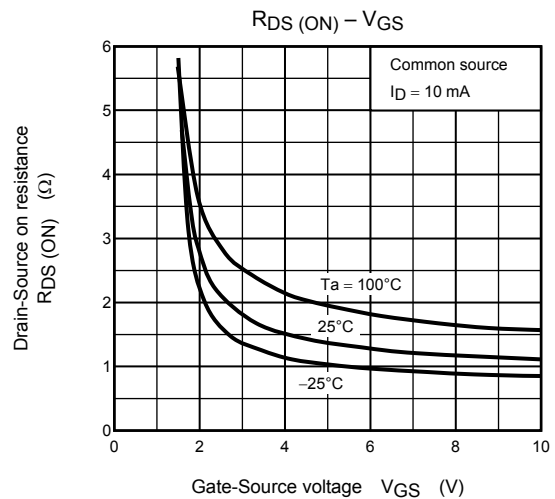
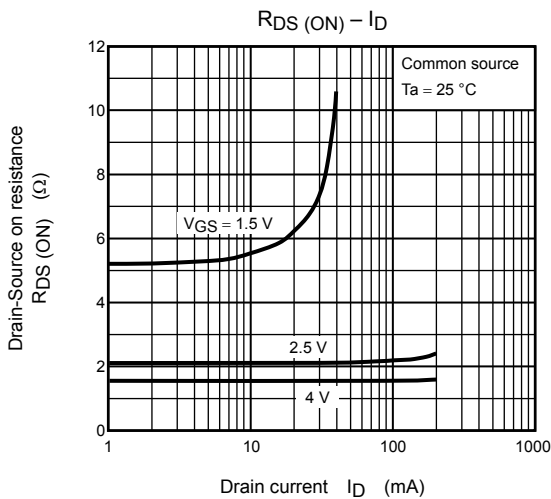
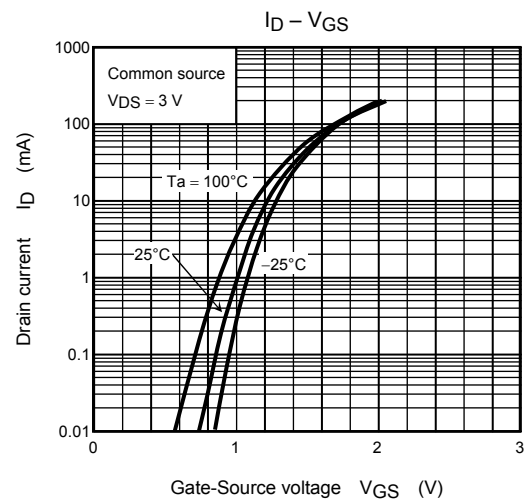
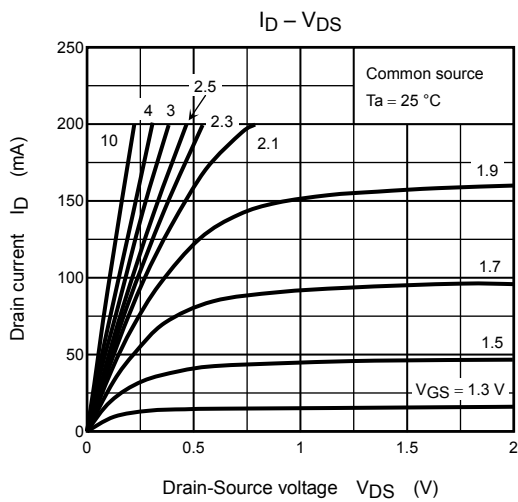
**Q1 (Pch MOSFET)**



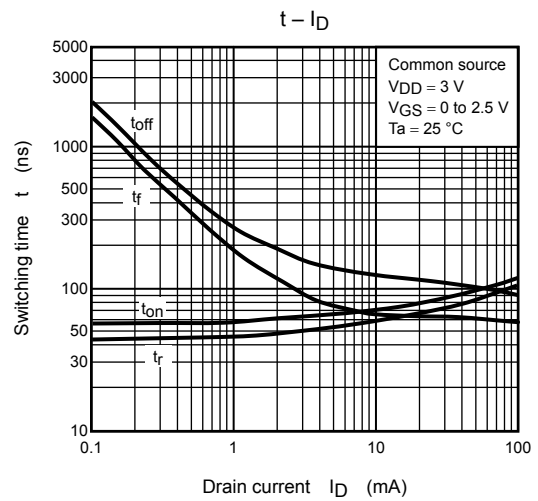
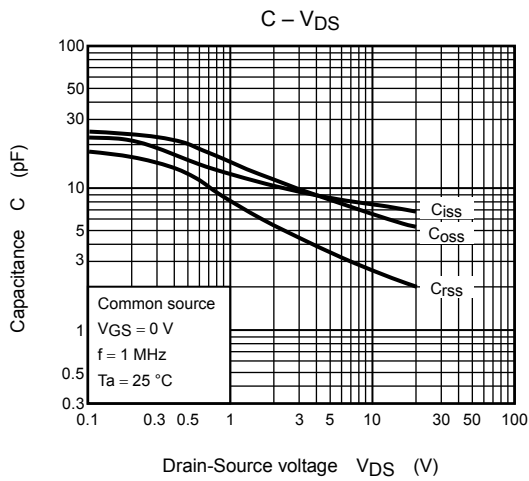
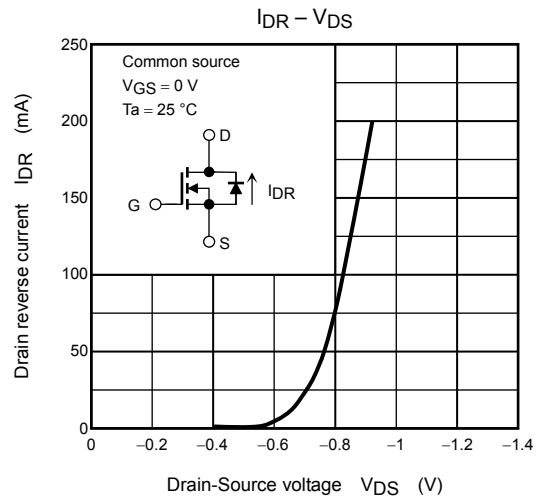
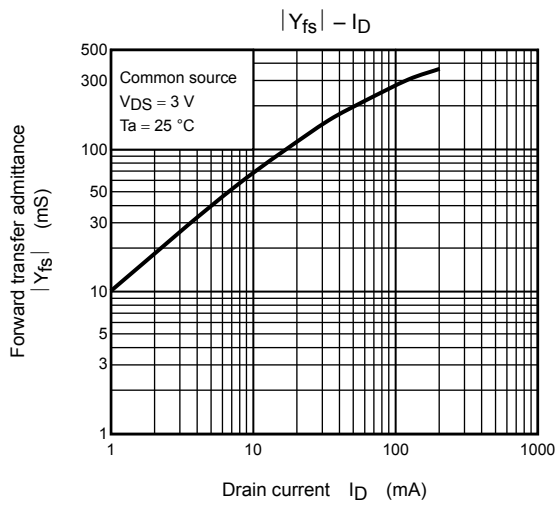
## Q1 (Pch MOSFET)



## Q2 (Nch MOSFET)



## Q2 (Nch MOSFET)



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